## IN THE CLAIMS:

Please cancel claims 1 to 5 and 14 to 27 without prejudice and amend the claims as follows:		
1. (canceled)		
2. (canceled)		
3. (canceled)		
4. (canceled)		
5. (canceled)		
6. (currently amended) A method for producing <b>a</b> the quartz glass article according to claim 1,		
for producing an optical component, the method comprising the steps of:		
providing a quartz glass cylinder having an inner bore therein,		
mechanically treating the inner bore to the a final dimension; and then		
applying an etching treatment to the inner bore,		
wherein the step of mechanically treating the inner bore comprises a plurality of		
removal processes each with a successively smaller removal depth such that,		
wherein the inner bore has subsurface cracks therein, and all of the subsurface		

<u>cracks in the inner bore have depths</u> of not more than 2 mm after the last removal process, and

wherein the inner bore is subsequently subjected to the etching treatment so as to produce an etching removal with a depth of not more than 50 µm, and such that the inner bore has an etched structure that has cracks therein, all of said cracks having a depth of not more than 2.0 mm and a width of not more than 100 µm.

- 7. (previously presented) The method according to claim 6, wherein the etching treatment yields an etching removal with a depth of not more than 25  $\mu$ m.
- 8. (previously presented) The method according to claim 6, wherein the etching treatment yields an etching removal with a depth of not more than  $10 \mu m$ .
- 9. (previously presented) The method according to claim 6, wherein the etching treatment yields an etching removal with a depth of at least  $2.5 \mu m$ .
- 10. (previously presented) The method according to claim 6, wherein the etching treatment includes a first etching step in a first etching solution containing hydrofluoric acid, and a second etching step in a second etching solution containing nitric acid.
- 11. (previously presented) The method according to claim 6, wherein the etching treatment is carried out at a mean etching rate of not more than 3 µm/min.

	12. (previously presented) The method according to claim 11, wherein the mean etching rate is not more than 1 $\mu$ m/min.
	13. (previously presented) The method according to claim 11, wherein the mean etching rate is not more than 0.1 $\mu$ m/min.
	14. (canceled)
	15. (canceled)
•	16. (canceled)
	17. (canceled)
	18. (canceled)
	19. (canceled)
	20. (canceled)
	21. (canceled)
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- 22. (canceled)
- 23. (canceled)
- 24. (new) The method according to claim 6, and further comprising inserting a core rod in the inner bore of the quartz glass cylinder, and forming a preform from said core rod and said quartz glass cylinder.